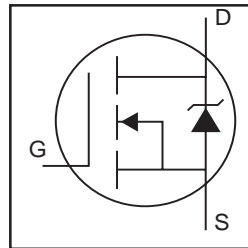


HEXFET® Power MOSFET Die in Wafer Form



200 V  
 Size 4.0  
 $R_{ds(on)}=0.18\Omega$   
 5" Wafer

**Electrical Characteristics ( Wafer Form )**

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200V Min.	$V_{GS} = 0V, I_D = 100\mu A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	0.180 $\Omega$ Max.	$V_{GS} = 10V, I_D = 10A$
$V_{GS(th)}$	Gate Threshold Voltage	2.3V Min., 4.0V Max.	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	25 $\mu A$ Max.	$V_{DS} = 200V, V_{GS} = 0V, T_J = 25^\circ C$
$I_{GSS}$	Gate-to-Source Leakage	$\pm 10\mu A$ Max.	$V_{GS} = \pm 20V$
$T_J$	Operating Junction and	125 $^\circ C$ Max.	
$T_{STG}$	Storage Temperature Range		

**Mechanical Data**

Nominal Backmetal Composition, Thickness:	Cr-NiV-Ag ( 1kA°-2kA°-2.5kA° )
Nominal Front Metal Composition, Thickness:	99% Al, 1% Si (0.004 mm)
Dimensions:	0.147" x 0.201" ( 3.73mm x 5.11 mm)
Wafer Diameter:	125mm with 100 flat
Wafer thickness:	0.375mm + / -0.020mm
Relevant Die Mechanical Dwg. Number	01-5331
Minimum Street Width	0.084 mm
Reject Ink Dot Size	0.51mm Diameter Minimum
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination
Recommended Die Attach Conditions	For optimum electrical results, die attach temperature should not exceed 300C

Reference Standard IR packaged part ( for design ) : IRF640

**Die Outline**

